

## 1. General description

Planar passivated four quadrant triac in a SOT82 (SIP3) plastic package intended for use in general purpose bidirectional switching and phase control applications.

## 2. Features and benefits

- High blocking voltage capability
- Planar passivated for voltage ruggedness and reliability
- Less sensitive gate for improved noise immunity
- Triggering in all four quadrants
- Compact package

## 3. Applications

- General purpose low power motor control
- Home appliances
- Industrial process control

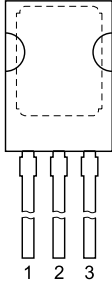

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Values			Unit
<b>Absolute maximum rating</b>						
$V_{DRM}$	repetitive peak off-state voltage		600			V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{mb} \leq 107\text{ °C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>	4			A
$I_{TSM}$	non-repetitive peak on-state current	full sine wave; $T_{j(initial)} = 25\text{ °C}$ ; $t_p = 20\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a>	25			A
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$I_{GT}$	gate trigger current	$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G+; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 7</a>	-	5	35	mA
		$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G-; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 7</a>	-	8	35	mA
		$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G-; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 7</a>	-	11	35	mA
		$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G+; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 7</a>	-	30	70	mA

## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1		 sym051
2	T2	main terminal 2		
3	G	gate		
mb	T2	mounting base; main terminal 2		

## 6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BT134-600	SIP3	plastic single-ended package; 3 leads (in-line)	SOT82

## 7. Marking

Table 4. Marking codes

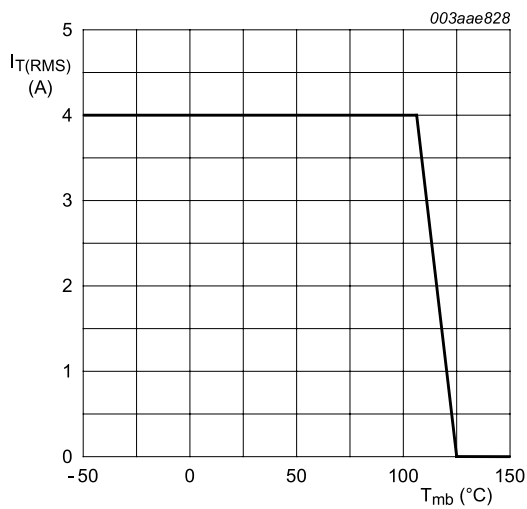
Type number	Marking codes
BT134-600	BT134-600

## 8. Limiting values

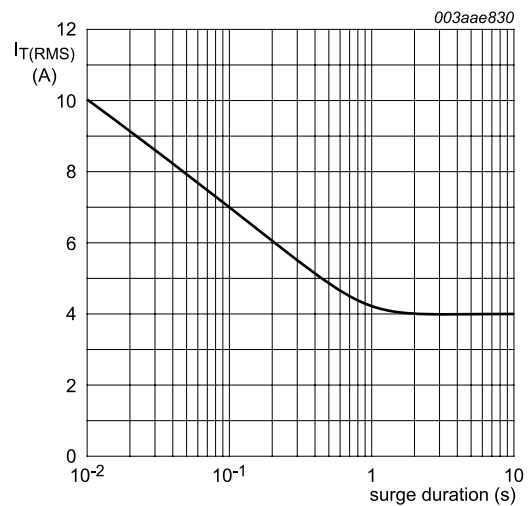
**Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
$V_{DRM}$	repetitive peak off-state voltage		600	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{mb} \leq 107\text{ }^{\circ}\text{C}$ ; <a href="#">Fig 1</a> ; <a href="#">Fig 2</a> ; <a href="#">Fig 3</a>	4	A
$I_{TSM}$	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25\text{ }^{\circ}\text{C}$ ; $t_p = 20\text{ ms}$ ; <a href="#">Fig 4</a> ; <a href="#">Fig 5</a>	25	A
		full sine wave; $T_{j(init)} = 25\text{ }^{\circ}\text{C}$ ; $t_p = 16.7\text{ ms}$	27	A
$I^2t$	$I^2t$ for fusing	$t_p = 10\text{ ms}$ ; SIN	3.1	$\text{A}^2\text{s}$
$di_T/dt$	rate of rise of on-state current	$I_G = 70\text{ mA}$	50	$\text{A}/\mu\text{s}$
		$I_G = 70\text{ mA}$	50	$\text{A}/\mu\text{s}$
		$I_G = 70\text{ mA}$	50	$\text{A}/\mu\text{s}$
		$I_G = 140\text{ mA}$	10	$\text{A}/\mu\text{s}$
$I_{GM}$	peak gate current		2	A
$P_{GM}$	peak gate power		5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	0.5	W
$T_{stg}$	storage temperature		-40 to 150	$^{\circ}\text{C}$
$T_j$	junction temperature		125	$^{\circ}\text{C}$



**Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values**



$f = 50\text{ Hz}$ ;  $T_{mb} \leq 107\text{ }^{\circ}\text{C}$

**Fig. 2. RMS on-state current as a function of surge duration; maximum values**

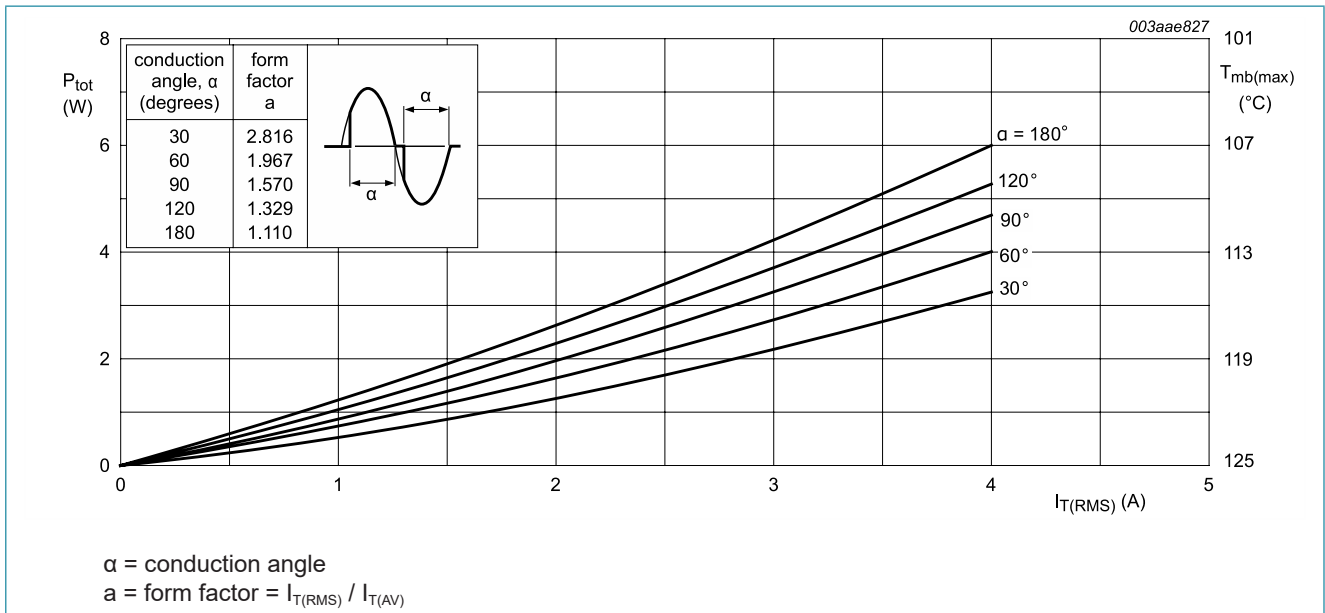


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

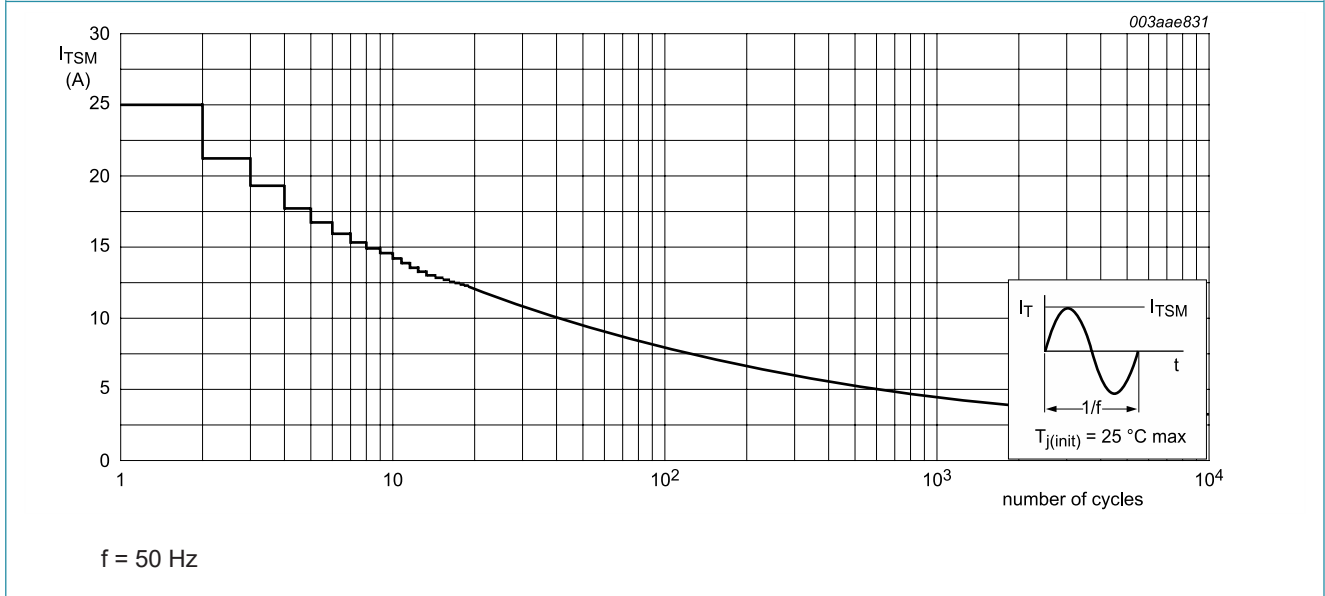


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

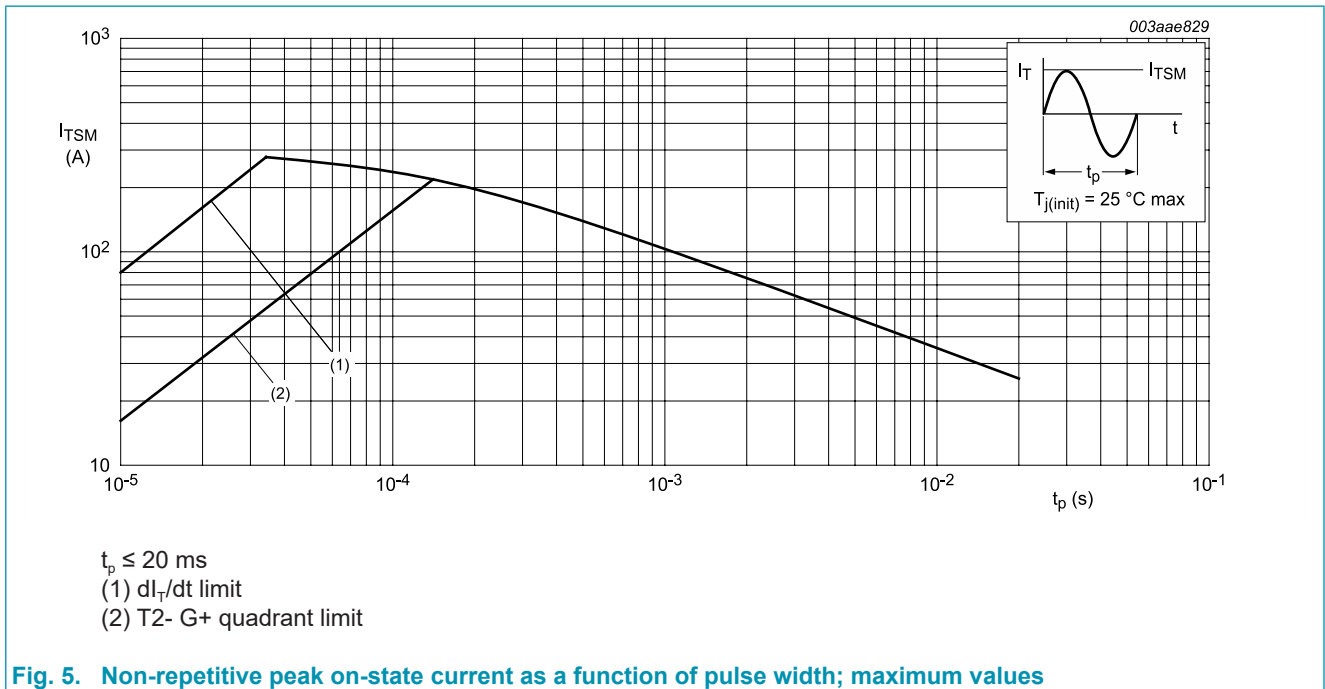
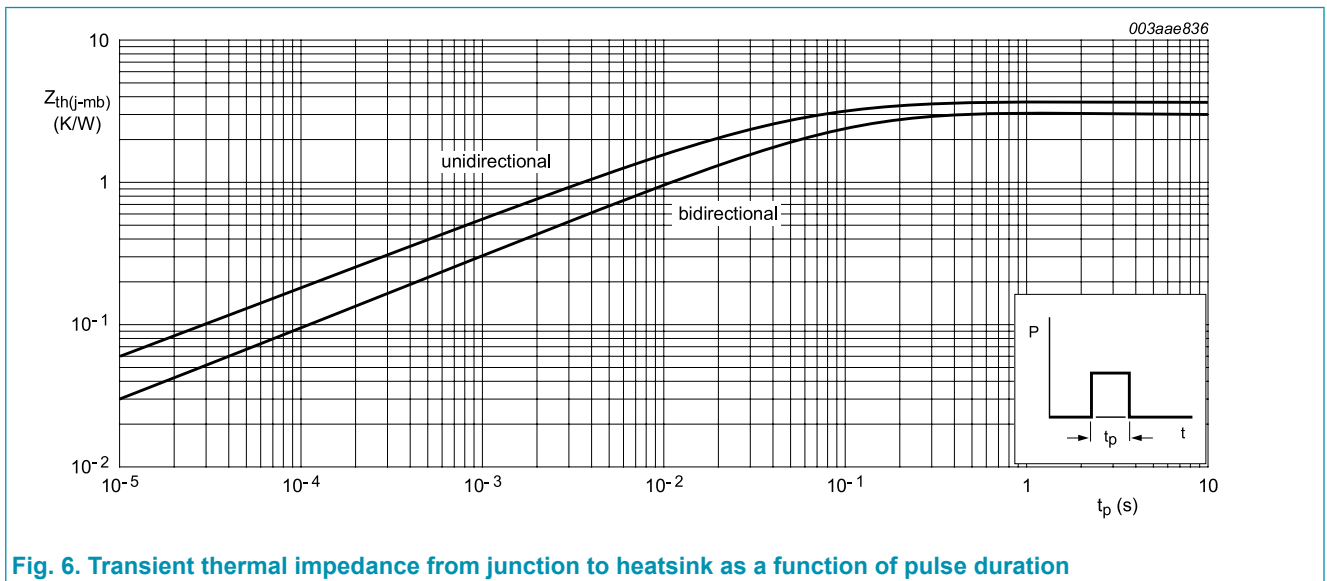


Fig. 5. Non-repetitive peak on-state current as a function of pulse width; maximum values

## 9. Thermal characteristics

Table 6. Thermal characteristics

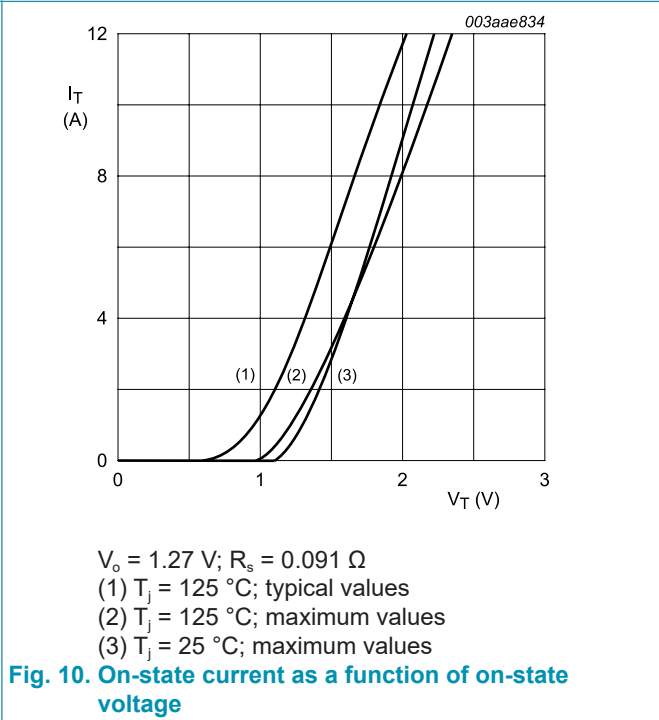
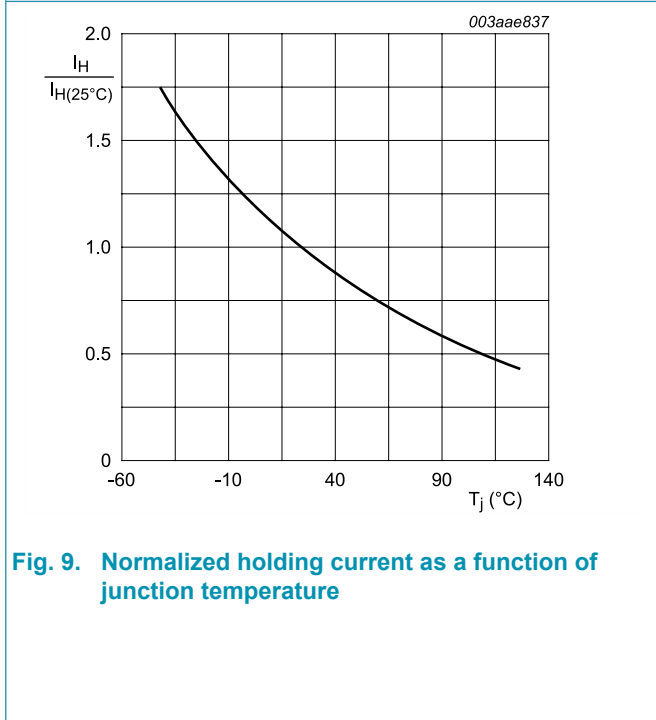
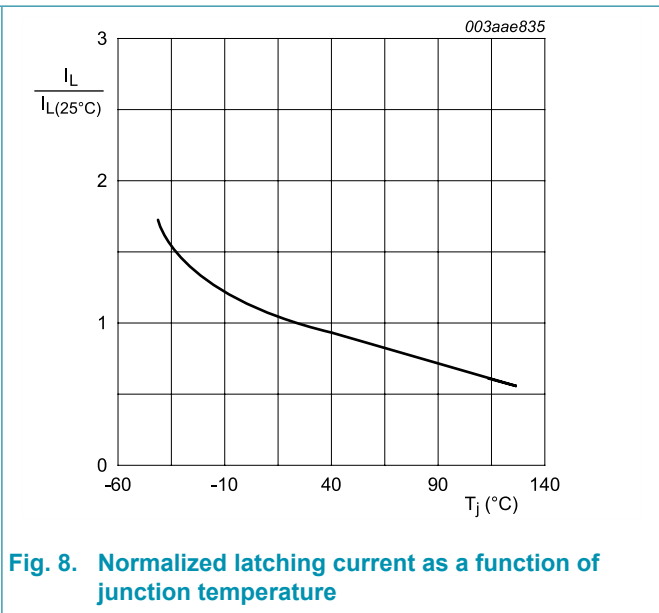
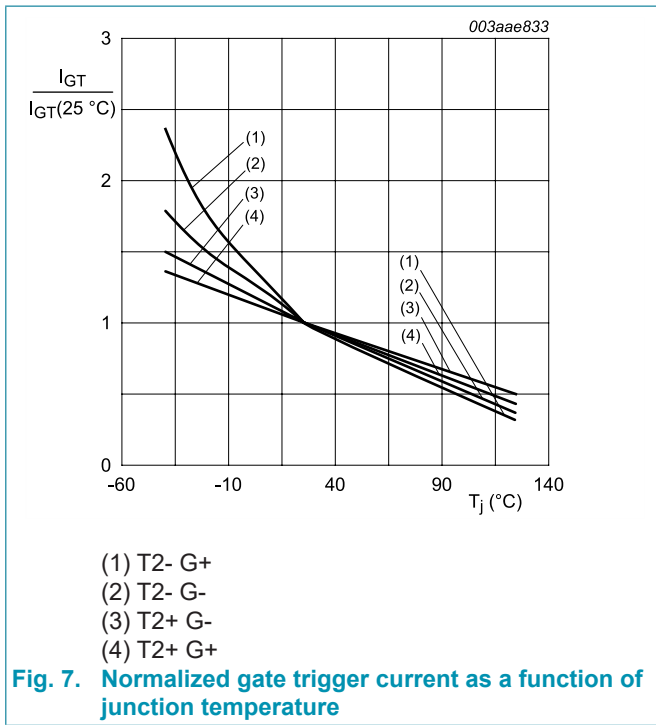
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to mounting base	half cycle; Fig 6	-	-	3.7	K/W
		half cycle; Fig 6	-	-	3	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	100	-	K/W



## 10. Characteristics

Table 8. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$I_{GT}$	gate trigger current	$V_D = 12\text{ V}; I_T = 0.1\text{ A}; T2+ G+;$ $T_J = 25\text{ }^\circ\text{C};$ <a href="#">Fig. 7</a>	-	5	35	mA
		$V_D = 12\text{ V}; I_T = 0.1\text{ A}; T2+ G-;$ $T_J = 25\text{ }^\circ\text{C};$ <a href="#">Fig. 7</a>	-	8	35	mA
		$V_D = 12\text{ V}; I_T = 0.1\text{ A}; T2- G-;$ $T_J = 25\text{ }^\circ\text{C};$ <a href="#">Fig. 7</a>	-	11	35	mA
		$V_D = 12\text{ V}; I_T = 0.1\text{ A}; T2- G+;$ $T_J = 25\text{ }^\circ\text{C};$ <a href="#">Fig. 7</a>	-	30	70	mA
$I_L$	latching current	$V_D = 12\text{ V}; I_G = 0.1\text{ A}; T2+ G+;$ $T_J = 25\text{ }^\circ\text{C};$ <a href="#">Fig. 8</a>	-	7	20	mA
		$V_D = 12\text{ V}; I_G = 0.1\text{ A}; T2+ G-;$ $T_J = 25\text{ }^\circ\text{C};$ <a href="#">Fig. 8</a>	-	16	30	mA
		$V_D = 12\text{ V}; I_G = 0.1\text{ A}; T2- G-;$ $T_J = 25\text{ }^\circ\text{C};$ <a href="#">Fig. 8</a>	-	5	20	mA
		$V_D = 12\text{ V}; I_G = 0.1\text{ A}; T2- G+;$ $T_J = 25\text{ }^\circ\text{C};$ <a href="#">Fig. 8</a>	-	7	30	mA
$I_H$	holding current	$V_D = 12\text{ V}; T_J = 25\text{ }^\circ\text{C};$ <a href="#">Fig. 9</a>	-	5	15	mA
$V_T$	on-state voltage	$I_T = 5\text{ A}; T_J = 25\text{ }^\circ\text{C};$ <a href="#">Fig. 10</a>	-	1.4	1.7	V
$V_{GT}$	gate trigger voltage	$V_D = 12\text{ V}; I_T = 0.1\text{ A}; T_J = 25\text{ }^\circ\text{C};$ <a href="#">Fig. 11</a>	-	0.7	1	V
		$V_D = 400\text{ V}; I_T = 0.1\text{ A}; T_J = 125\text{ }^\circ\text{C};$ <a href="#">Fig. 11</a>	0.25	0.4	-	V
$I_D$	off-state current	$V_D = 600\text{ V}; T_J = 125\text{ }^\circ\text{C}$	-	0.1	0.5	mA
<b>Dynamic characteristics</b>						
$dV_D/dt$	rate of rise of off-state voltage	$V_{DM} = 402\text{ V}; T_J = 125\text{ }^\circ\text{C}; (V_{DM} = 67\%$ of $V_{DRM});$ exponential waveform; gate open circuit	100	250	-	V/ $\mu$ s
$dV_{com}/dt$	rate of change of commutating voltage	$V_D = 400\text{ V}; T_J = 95\text{ }^\circ\text{C}; I_T = 4\text{ A};$ $dl_{com}/dt = 1.8\text{ A/ms};$ gate open circuit	-	50	-	V/ $\mu$ s
$t_{gt}$	gate-controlled turn-on time	$V_D = 600\text{ V}; I_{TM} = 6\text{ A}; I_G = 0.1\text{ A};$ $dl_G/dt = 5\text{ A}/\mu\text{s}$	-	2	-	$\mu$ s





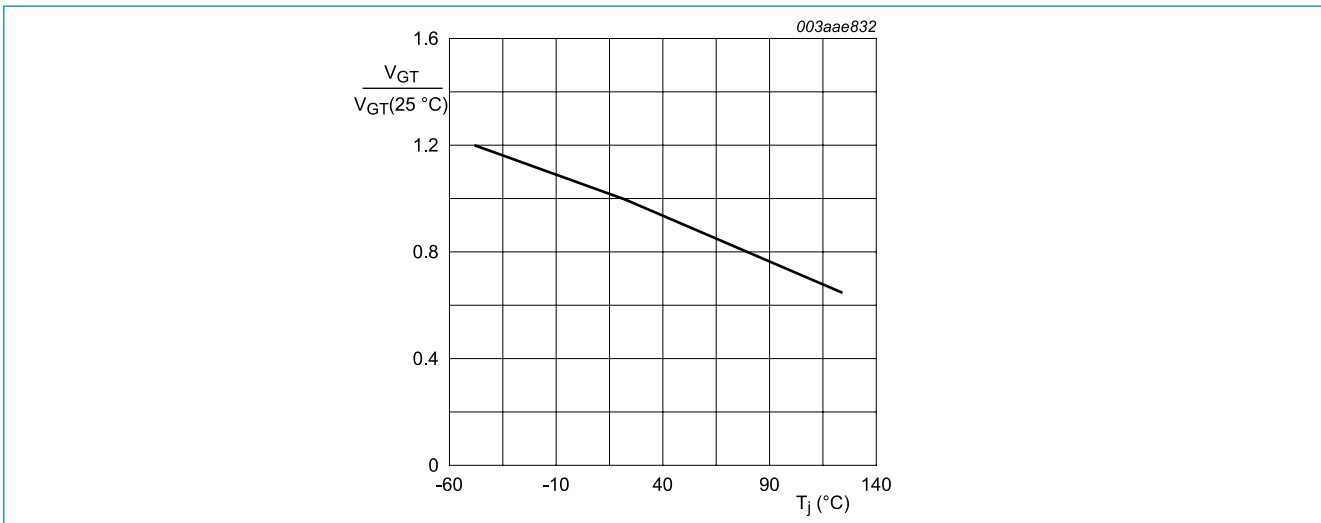
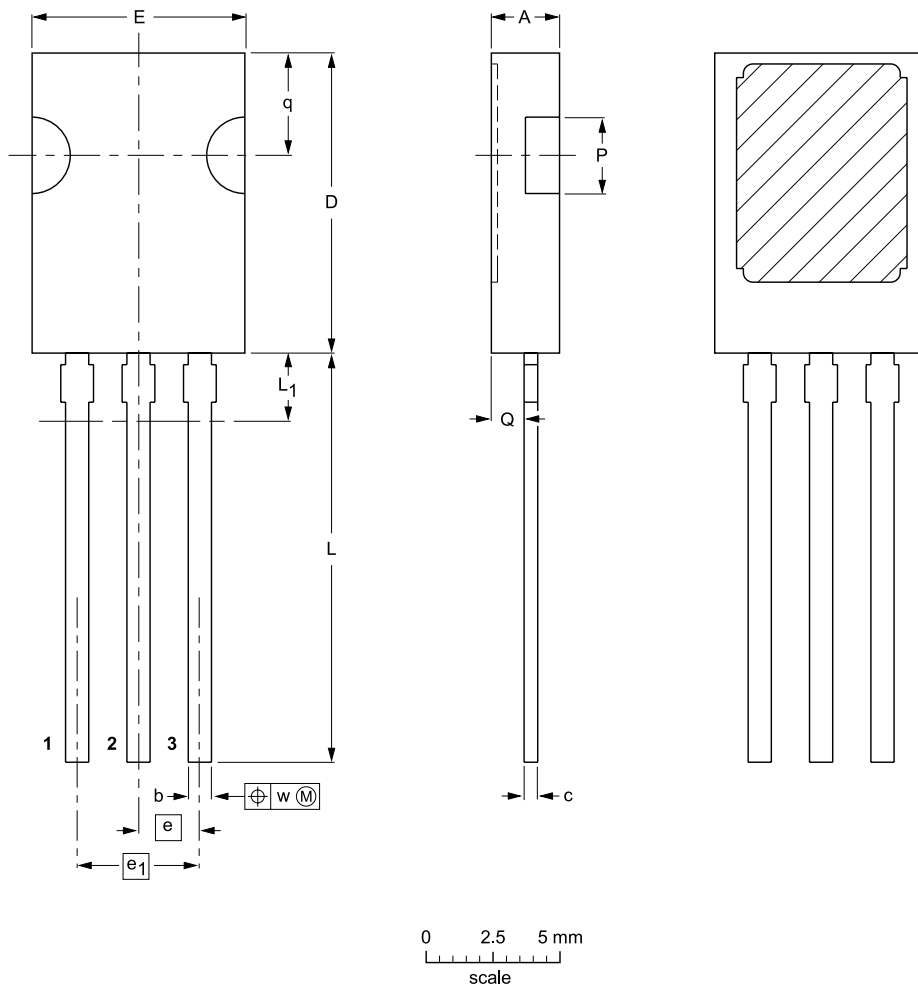


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

### 11. Package outline

Plastic single-ended package; 3 leads (in-line)

SOT82



DIMENSIONS (mm are the original dimensions)

UNIT	A	b	c	D	E	e	e <sub>1</sub>	L	L <sub>1</sub> <sup>(1)</sup> max.	P	Q	q	w
mm	2.8 2.3	0.88 0.65	0.58 0.47	11.1 10.5	7.8 7.2	2.29	4.58	16.5 15.3	2.54	3.1 2.5	1.5 0.9	3.9 3.5	0.254

**Note**

1. Terminal dimensions within this zone are uncontrolled to allow for body and terminal irregularities.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT82						97-06-11

## 12. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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